

Silicon NPN Power Transistors 2SD1274 2SD1274A 2SD1274B

DESCRIPTION

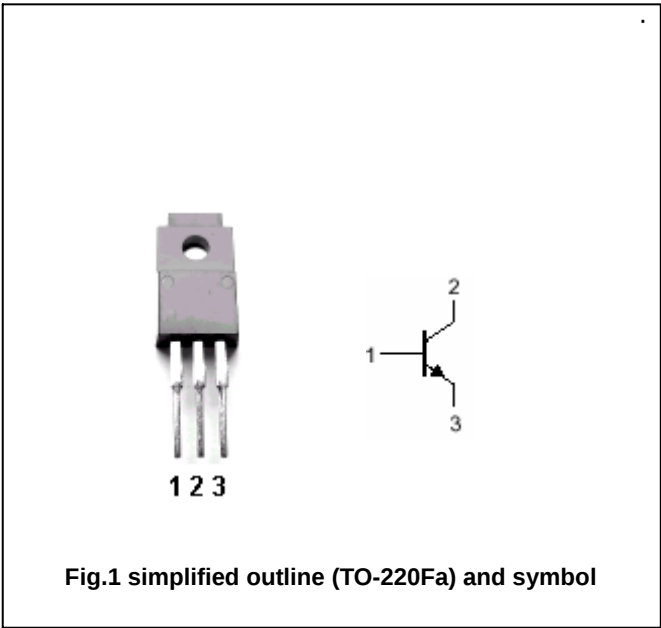
- With TO-220Fa package
- High V_{CBO}
- High speed switching

APPLICATIONS

- Power amplifier applicaitons

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings ($T_a=25\text{ }^{\circ}\text{C}$)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2SD1274	Open emitter	150	V
		2SD1274A		200	
		2SD1274B		250	
V_{CEO}	Collector-emitter voltage		Open base	80	V
V_{EBO}	Emitter-base voltage		Open collector	6	V
I_C	Collector current (DC)			5	A
P_C	Collector power dissipation		$T_C=25$	40	W
			$T_a=25$	2	
T_j	Junction temperature			150	
T_{stg}	Storage temperature			-55~150	

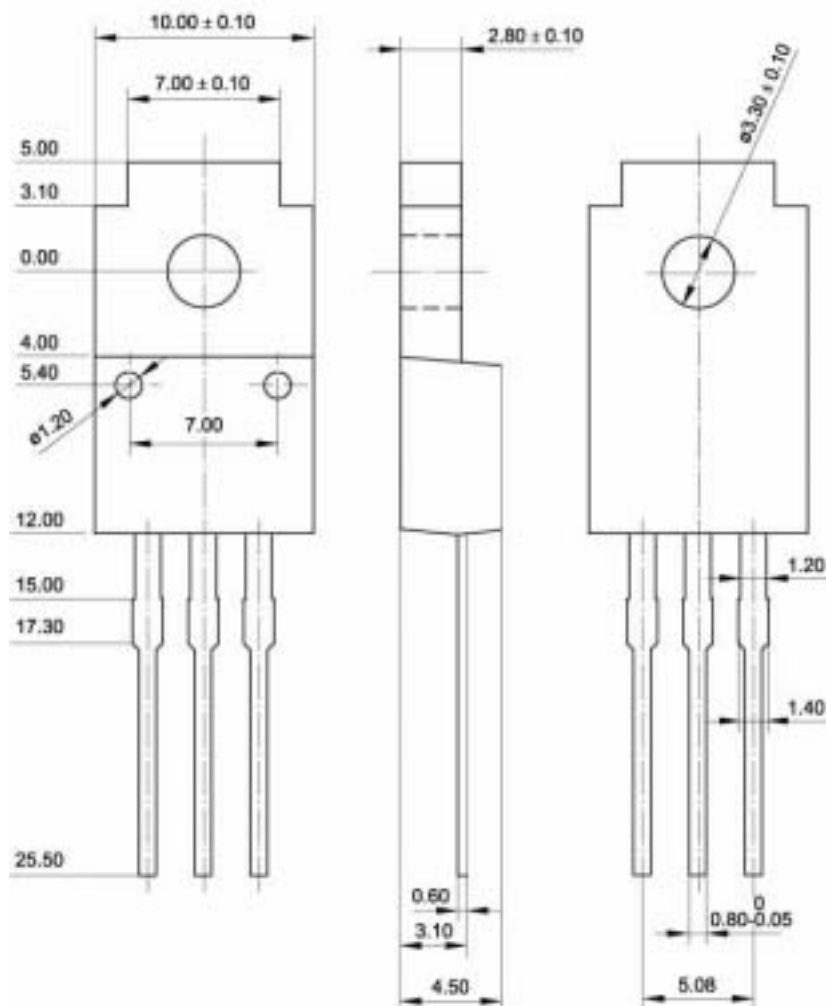
Silicon NPN Power Transistors**2SD1274 2SD1274A 2SD1274B****CHARACTERISTICS****T_j=25** unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage		I _C =0.2A, L=25mH	80			V
V _{(BR)EBO}	Emitter-base breakdown voltage		I _E =1mA, I _C =0	6			V
V _{CEsat}	Collector-emitter saturation voltage		I _C =5A; I _B =1A			1.6	V
V _{BE}	Base-emitter voltage		I _C =5A ; V _{CE} =4V			1.5	V
I _{CBO}	Collector cut-off current	2SD1274	V _{CB} =150V; I _E =0			1	mA
		2SD1274A	V _{CB} =200V; I _E =0				
		2SD1274B	V _{CB} =250V; I _E =0				
I _{EBO}	Emitter cut-off current		V _{EB} =5V; I _C =0			50	μ A
h _{FE}	DC current gain		I _C =5A ; V _{CE} =4V	14			
f _T	Transition frequency		I _C =0.5A ; V _{CE} =10V		40		MHz
t _f	Fall time		I _C =5A ; I _{B1} =0.8A V _{EB} =-5V			1.0	μ s

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PACKAGE OUTLINE

Fig.2 Outline dimensions (unindicated tolerance: ± 0.15 mm)